

**What is claimed is:**

1. A semiconductor device comprising:  
a wiring pattern and a plurality of dummy patterns  
different from the wiring pattern; and  
an insulating film formed on the wiring pattern and  
the dummy patterns by a chemical vapor deposition method  
and planarized by CMP,  
wherein the dummy patterns are provided with  
pattern non-forming regions each having a width filled by  
plus sizing of the insulating film upon formation of the  
insulating film.
2. A semiconductor device according to claim 1,  
wherein the pattern non-forming regions of the dummy  
patterns are formed in stripe form.
3. A semiconductor device according to claim 1,  
wherein the pattern non-forming regions of the dummy  
patterns are formed in character or graphical form.
4. A semiconductor device according to claim 1,  
wherein the pattern non-forming regions of the dummy  
patterns are shaped in character or graphical forms  
different every said dummy patterns.
5. A semiconductor device according to claim 1,

wherein the dummy patterns are square.

6. A semiconductor device according to claim 1,  
wherein the dummy patterns are arranged in lattice form.